

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

3SK264 — VHF Tuner, High-Frequency Amplifier Applications

Features

- · Enhancement type
- Easy AGC (Cut off at VG2S=0V)
- · Small noise figure
- · Excels in cross modulation characteristics

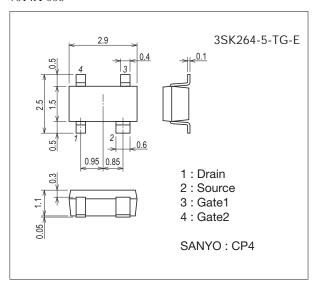
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DS}		15	V
Gate1-to-Source Voltage	V _{G1S}		±8	V
Gate2-to-Source Voltage	V _{G2S}		±8	V
Drain Current	ID		30	mA
Allowable Power Dissipation	PD		200	mW
Channel Temperature	Tch		125	°C
Storage Temperature	Tstg		-55 to +125	°C

Package Dimensions

unit : mm (typ) 7014A-006



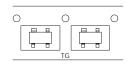
Product & Package Information

• Package : CP4

• JEITA, JEDEC : SC-61, SC-82AB, SOT-143, SOT-343

• Minimum Packing Quantity: 3,000 pcs./reel

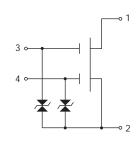
Packing Type: TG



Marking



Electrical Connection



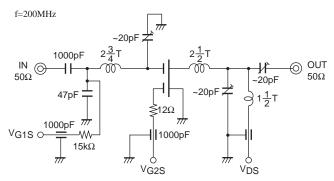
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Syllibol	Conditions	min	typ	max	UIII	
Drain-to-Source Voltage	VDS	VG1S=0V, VG2S=0V, IDS=100μA 15			V		
Gate1-to-Source Cutoff Voltage	V _{G1S} (off)	V _{DS} =6V, V _{G2S} =4V, I _D =100μA	0	0.7	1.3	V	
Gate2-to-Source Cutoff Voltage	V _{G2S} (off)	V _{DS} =6V, V _{G1S} =3V, I _D =100μA	0.1	0.9	1.6	V	
Gate1-to-Source Leakage Current	lG1SS	V _{G1S} =±6V, V _{G2S} =V _{DS} =0V		±50	nA		
Gate2-to-Source Leakage Current	IG2SS	VG2S=±6V, VG1S=VDS=0V	VG2S=±6V, VG1S=VDS=0V		±50	nA	
Zero-Gate Voltage Drain Current	I _{DSX}	V _{DS} =6V, V _{G1S} =1.5V, V _{G2S} =4V	5.0*		24.0*	mA	
Forward Transfer Admittance	yfs	V _{DS} =6V, I _D =10mA, V _{G2S} =4V, f=1kHz	17			mS	
Input Capacitance	Ciss	Voc 6V Vote 0V Voce 4V f 1MHz		2.5		pF	
Reverse Transfer Capacitance	Crss	V _{DS} =6V, V _{G1S} =0V, V _{G2S} =4V, f=1MHz		0.015	0.03	pF	
Power Gain	PG	V _{DS} =6V, I _D =10mA, V _{G2S} =4V, f=200MHz 20 23			dB		
Noise Figure	NF	V _{DS} =6V, I _D =10mA, V _{G2S} =4V, f=200MHz 1.1 2		2.2	dB		

* : The 3SK264 is classified by $I_{\mbox{DSX}}$ as follows : (unit : mA)

Rank	5	6		
IDSX	5.0 to 12.0	10.0 to 24.0		

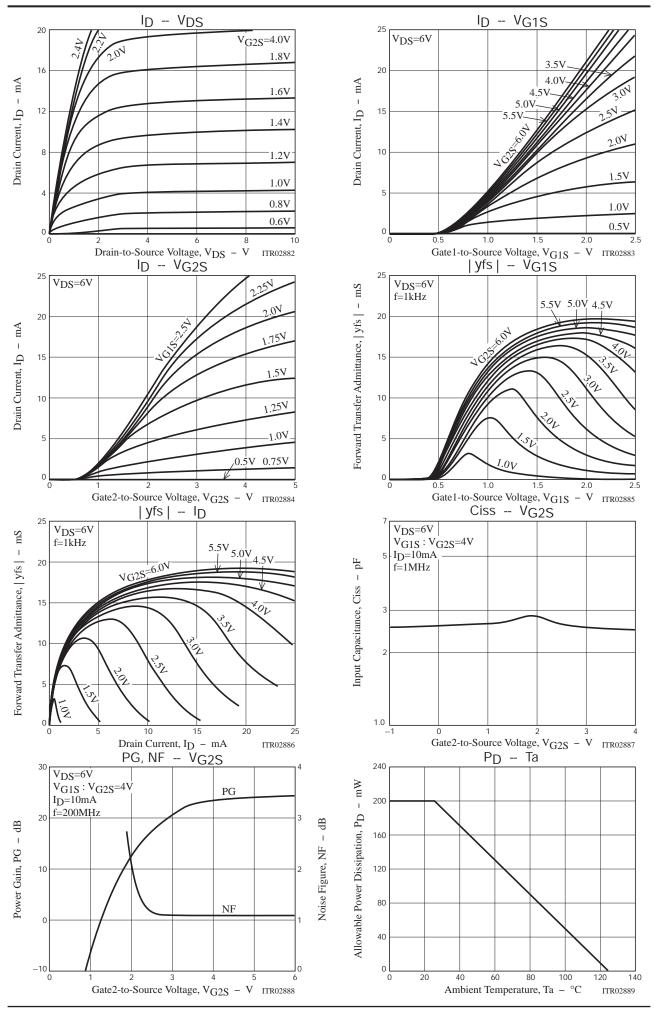
PG, NF Specified Test Circult



L: 1mmØ enamel wire 10mmØ

Ordering Information

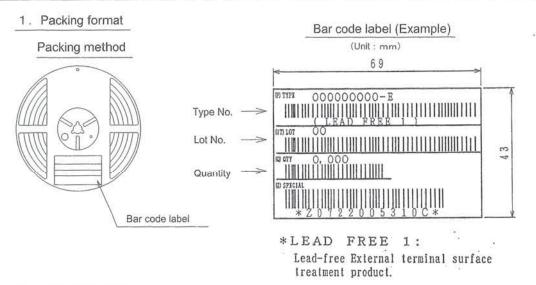
Device	Device Package		memo	
3SK264-5-TG-E	CP4	3,000pcs./reel	Pb Free	



Embossed Taping Specification

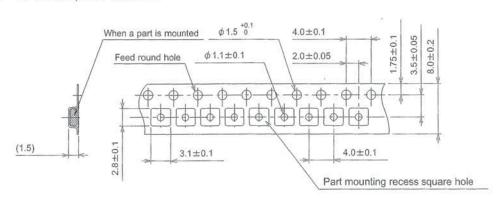
3SK264-5-TG-E

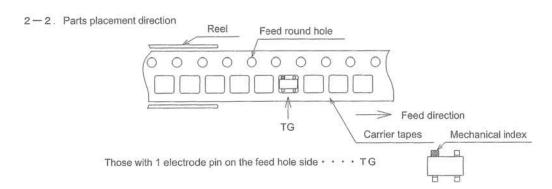
Storage package Outline name Carrier tape Type number	Maximum Number of devices contained (pcs.)			Packing format		
	Type number	Reel	Inner box	Outer box	Inner box BOX (C-1)	Outer box BOX (A-7)
CP4	CP4	3,000	15,000	90,000	5 reels contained Dimensions:mm(external) . 1 8 3 × 7 2 × 1 8 5	6 inner boxes contained Dimensions:mm(external) 4 4 0 × 1 9 5 × 2 1 0



2. Taping structure

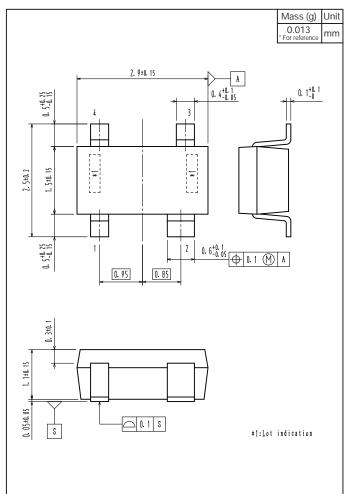
2-1. Carrier tape size (Unit : mm)



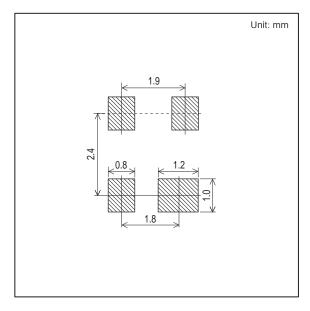


Outline Drawing

3SK264-5-TG-E



Land Pattern Example



Note on usage: Since the 3SK264 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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